EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2765	(Integrated circuit or IC or chip) SAME (first or primary or 1ST) SAME (connect$3 or coupl$3 or tie) SAME (input) SAME (output) SAME (clamp$3 or secure$3 or latch$3) SAME (device or design or apparatus)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 18:55
S2	2756	(Integrated circuit or IC or chip) SAME (first or primary or 1ST) SAME (connect$3 or coupl$3) SAME (input) SAME (output) SAME (clamp$3 or secure$3 or latch$3) SAME (device or design or apparatus)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 18:56
S3	29	(Integrated circuit or IC or chip) SAME (first or primary or 1ST) SAME (connect$3 or coupl$3) SAME (input) SAME (output) SAME (clamp$3 or secure$3 or latch$3) SAME (device or design or apparatus) AND 361/56. CCLS.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 18:59
S4	4	(Integrated circuit or IC or chip) SAME (first or primary or 1ST) SAME (connect$3 or coupl$3) SAME (input) SAME (output) SAME (clamp$3 or secure$3 or latch$3) SAME (transistor) SAME (pad) SAME (device or design or apparatus) AND 361/56. CCLS.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 19:03
S5	7	(Integrated circuit or IC or chip) SAME (first or primary or 1ST) SAME (connect$3 or coupl$3) SAME (input) SAME (output) SAME (clamp$3 or secure$3 or latch$3) SAME (transistor) SAME (pad) SAME (device or design or apparatus) AND "361"/$. CCLS.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 19:03

S6	1	(Integrated circuit or IC or chip) SAME (first transistor) same pad same (control output) same (control input) same (clamping device)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 19:17
S7	1	(Integrated circuit or IC or chip) SAME (first transistor) same pad same (clamping device)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 19:19
S8	221	(Integrated circuit or IC or chip) SAME (first transistor) same pad	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 19:19
S9	38	(Integrated circuit or IC or chip) SAME (first transistor) same pad and "361"/$.ccls.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 19:19
S10	1	(Integrated circuit or IC or chip) SAME (first transistor) same pad same clamping device and "361"/$.ccls.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 19:51
S11	1	(Integrated circuit or IC or chip) SAME (first transistor) same pad same clamp and "361"/$.ccls.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 19:51
S12	4	(Integrated circuit or IC or chip) SAME (first transistor) same pad same clamp$3 and "361"/$.ccls.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 19:52
S13	1	(Integrated circuit or IC or chip) SAME (first transistor) same pad same clamp and "361"/$.ccls.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 20:14
S14	0	(first transistor) same pad same clamp device	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 20:16
S15	21	(first transistor) same pad same clamp	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 20:17
S16	33	(first transistor) same clamp transistor	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 21:08
S17	2	(first transistor) same clamp transistor and pad	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 21:16

S18	1	(first transistor) same clamp transistor same pad	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 21:17
S19	1	(first transistor) same clamp transistor same PAD	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 21:17
S20	0	(first transistor) same clamp device same PAD	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 21:18
S21	3	(first transistor) same clamp circuit same PAD	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 21:18
S22	9	reference voltage same clamp circuit same PAD	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 21:44
S23	1	reference voltage same clamp transistor same PAD	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 21:46
S24	2	reference voltage same clamp device same PAD	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 21:46
S25	2984	(second transistor) same (first transistor) same (reference voltage)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 22:00
S26	86	(second transistor) same (first transistor) same (reference voltage) and (ESD or Electrostatic Discharge or electrostatic overstress or EOS)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 22:01
S27	26	(second transistor) same (first transistor) same (reference voltage) and (ESD or Electrostatic Discharge or electrostatic overstress or EOS) SAME series	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/08 23:09
S28	4	(second transistor) same (first transistor) same (reference voltage) and (ESD or Electrostatic Discharge or electrostatic overstress or EOS) and (in series)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 09:54

S29	2984	(second transistor) same (first transistor) same (reference voltage)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 09:55
S30	59	(second transistor) same (first transistor) same (reference voltage) and ESD	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 09:56
S31	1	(second transistor) same (first transistor) same (supply voltage or Vdd) and (ESD or Electrostatic Discharge or electrostatic overstress or EOS) SAME resistor SAME transistor SAME time delay	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 10:25
S32	87	(second transistor) same (first transistor) same (supply voltage or Vdd) and (ESD or Electrostatic Discharge or electrostatic overstress or EOS) SAME resistor SAME transistor	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 10:26
S33	28	(second transistor) same (first transistor) same (supply voltage or Vdd) and (ESD or Electrostatic Discharge or electrostatic overstress or EOS) same time and delay	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 10:29
S34	188	(supply voltage or Vdd) and (ESD or Electrostatic Discharge or electrostatic overstress or EOS) same time near5 delay	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 10:31
S35	95	(supply voltage or Vdd) and (ESD or Electrostatic Discharge or electrostatic overstress or EOS) same time near5 delay same resistor	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 10:31
S36	47	(supply voltage or Vdd) and (ESD or Electrostatic Discharge or electrostatic overstress or EOS) same time near5 delay same resistor same transistor	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 10:32
S37	5	(supply voltage or Vdd) and (ESD or Electrostatic Discharge or electrostatic overstress or EOS) same time near5 delay same resistor same transistor same element	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 10:43
S38	13589	(time near3 delay) near5 element	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 10:45

S39	30	(time near3 delay) near5 element same (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 10:46
S40	54	(time delay element) and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 10:52
S42	872	(resistor) same transistor same series same (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 10:56
S43	154	(resistor) same transistor same series same (EOS or ESD) same (supply voltage or Vdd)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 10:57
S44	11	(resistor) same transistor same series same (EOS or ESD) same (supply voltage or Vdd) same delay	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 11:04
S45	2	(resistor) same transistor same series same (EOS or ESD) same (supply voltage or Vdd) same delay same capacitance	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 11:07
S46	4888	(time delay) same (element or circuit) same resistor same transistor	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 17:34
S47	20	(time delay) same (element or circuit) same resistor same transistor same (ESD or electrostatic discharge)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 17:35
S48	41	"5654862"	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 18:38
S49	6	(time delay) same (element or circuit) same resistor same transistor same capacit$3 same (ESD or electrostatic discharge)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 18:41
S50	3	(time delay) same (element or circuit) same (first transistor) same (second transistor) same (ESD or electrostatic discharge)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 18:45
S51	4	(time delay) same (element or circuit) same (first transistor) same (second transistor) and (ESD or electrostatic discharge)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 18:45

S52	2	(time delay) same (element or circuit) same (first transistor) same (second transistor) same (resistor) same (capacitance) and (ESD or electrostatic discharge)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 18:47
S53	2	(time delay) same (first transistor) same (second transistor) same (resistor) same (capacitance) and (ESD or electrostatic discharge)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 18:48
S54	42	(time delay) same (first transistor) same (second transistor) same (resistor) same (capacitance)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 18:48
S55	2	(time delay) same (element or circuit) same resistor same transistor same (ESD or electrostatic discharge) same (Vdd or supply voltage)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 18:54
S56	2	(time delay) same (element or circuit) same resistor same capacitance same (ESD or electrostatic discharge) same (Vdd or supply voltage)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 18:54
S57	2	(time delay) same resistor same capacitance same (ESD or electrostatic discharge) same (Vdd or supply voltage)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 19:00
S58	12	(time delay) same resistor same (ESD or electrostatic discharge) same (Vdd or supply voltage)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 19:00
S59	570	(time delay circuit) same (Vdd or supply voltage)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 19:17
S60	97	(time delay circuit) same (Vdd or supply voltage) and "361"/$.ccls.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 19:17
S61	3	(time delay circuit) same (Vdd or supply voltage) same (first transistor) same (second transistor) and "361"/$.ccls.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 19:18
S62	2	(time near3 delay) same (Vdd or supply voltage) same (first transistor) same (second transistor) and (ESD) and "361"/$.ccls.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 19:20

S63	36	("4716302" | "4855620" | "4859875" | "4864454" | "4989057" | "5051860" | "5157573" | "5170240" | "5208719" | "5237395" | "5311391").PN. OR ("5617283").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/12/09 19:54
S64	3	("4573168" | "5359211" | "5617283").PN. OR ("6885533").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/12/09 19:54
S65	1	"20030235022"	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/09 20:25
S66	11	(resistor) same transistor same series same (EOS or ESD) same (supply voltage or Vdd) same parasitic	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 13:18
S67	0	(clamping voltage device) same (parasitic transistor) and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 13:29
S68	0	(clamping voltage device) same (parasitic) and (transistor) and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 13:29
S69	3203	(parasitic) and (transistor) and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 13:29
S70	358	(parasitic transistor) and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 13:30
S71	570	(npn near5 parasitic near5 transistor) and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 13:40
S72	42	(npn parasitic transistor) and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 13:41
S73	0	(npn parasitic transistor) near5 (clamping voltage device) and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 13:45
S74	0	(npn parasitic transistor) near5 (clamping device) and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 13:45

S75	0	(npn parasitic transistor) near5 (clamp$3 device) and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 13:46
S76	0	(npn parasitic transistor) same (clamp$3 device) and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 13:46
S77	0	(npn parasitic transistor) same (clamp$3) same (device) and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 13:46
S78	0	(npn parasitic transistor) same (clamp$3) and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 13:46
S79	12	(npn parasitic transistor) and clamp$3 and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 13:47
S80	0	(npn parasitic transistor) same clamp$3 and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 13:57
S81	12	(npn parasitic transistor) and clamp$3 and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 14:00
S82	168	(parasitic transistor) and clamp$3 and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 14:16
S83	28	(parasitic transistor) same clamp$3 and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 14:16
S84	2	(parasitic transistor) near5 clamp$3 and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 14:19
S85	18	(parasitic transistor) same clamp$3 same circuit and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 14:27
S86	162	time same delay same resistor same transistor same capacit$3 same supply and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 14:52
S87	85	time same delay same resistor same transistor same capacit$3 same supply same series and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 14:52

S88	44	time same delay same resistor same transistor same capacit$3 same supply same series and (EOS or ESD) and (Integrated circuit or IC or chip)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 14:58
S89	1549	resistor same transistor same series and (EOS or ESD) and (Integrated circuit or IC or chip)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 15:00
S90	9	resistor same transistor same (in series) and (EOS or ESD) and (Integrated circuit or IC or chip)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 15:00
S91	2007	resistor same transistor same capacit$3 and (EOS or ESD) and (Integrated circuit or IC or chip)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 15:01
S92	202	resistor same transistor same capacit$3 same time same delay and (EOS or ESD) and (Integrated circuit or IC or chip)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 15:02
S93	1	resistor and transistor and capacitance and "4303894".pn.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 15:47
S94	16194	resistor same transistor same capacitance and ((supply voltage) or Vdd or power)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 15:55
S95	56	S92 and (@ad<"20030630" or @rlad<"20030630")	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 16:00
S96	22	S95 and "361".clas.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 16:06
S97	1	"6031405".pn.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 16:10
S98	334	(clamp$3) same (thyristor or SCR) and (transistor) and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 17:16
S99	91	(clamp$3) same (thyristor) and (transistor) and (EOS or ESD)	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 17:25

S100	22	S96 and (@ad<"20030630" or @rlad<"20030630")	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 17:26
S101	223	S98 and (@ad<"20030630" or @rlad<"20030630")	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 17:28
S102	67	S99 and (@ad<"20030630" or @rlad<"20030630")	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 17:28
S103	43	thyristor same clamp$3 same transistor and (ESD or EOS) and (@ad<"20030630" or @rlad<"20030630")	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 17:45
S104	20	thyristor same clamp$3 same device same transistor and (ESD or EOS) and (@ad<"20030630" or @rlad<"20030630")	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 18:02
S105	68	thyristor same clamp$3 and (ESD or EOS) and (@ad<"20030630" or @rlad<"20030630")	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 18:05
S106	1	"20030235022"	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 18:48
S107	568	(reference voltage) same (third transistor) same (fourth transistor) and (@ad<"20030630" or @rlad<"20030630")	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 19:13
S108	12	(reference voltage) same (third transistor) same (fourth transistor) and ("361"/$.ccls.) and (@ad<"20030630" or @rlad<"20030630")	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 19:14
S109	1	"6912109".pn.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 19:57
S110	1	"6031405".pn.	US-PGPUB; USPAT; USOCR; IBM_TDB	ADJ	ON	2007/12/10 19:58

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